

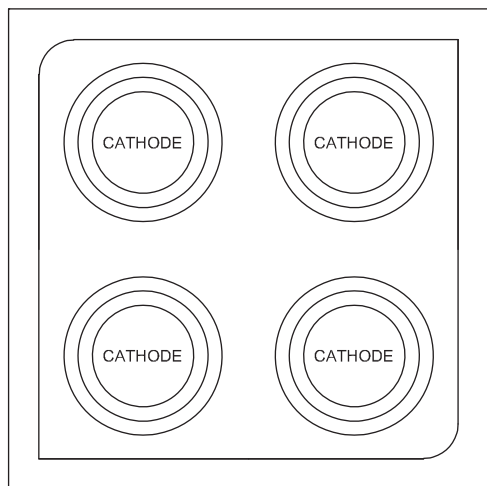
PROCESS CPZ33R
Transient Voltage Suppressor
12 Volt Quad TVS Chip



PROCESS DETAILS

Die Size	14.2 x 14.2 MILS
Die Thickness	3.9 MILS
Cathode Bonding Pad Areas (4)	4.7 MILS DIAMETER EACH
Top Side Metalization	Al - 13,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE ANODE R0

GROSS DIE PER 5 INCH WAFER

84,926

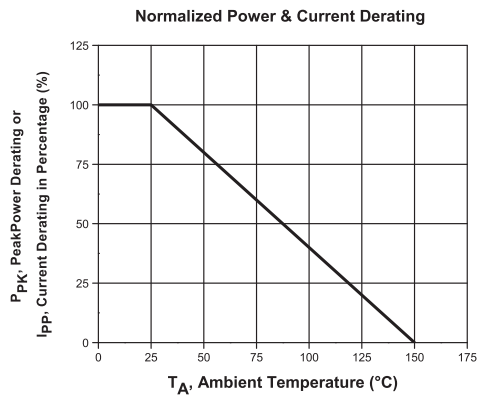
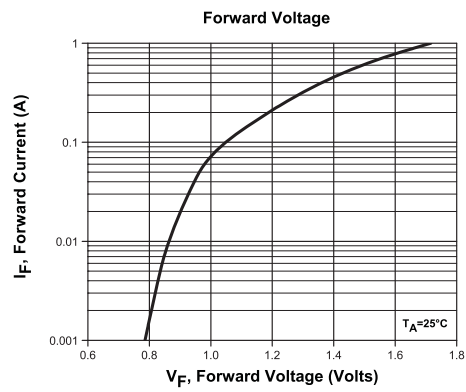
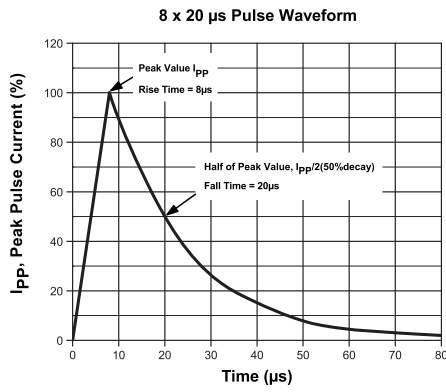
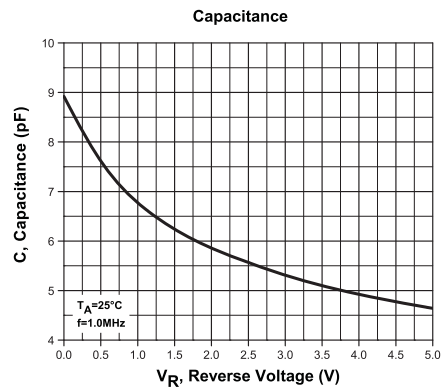
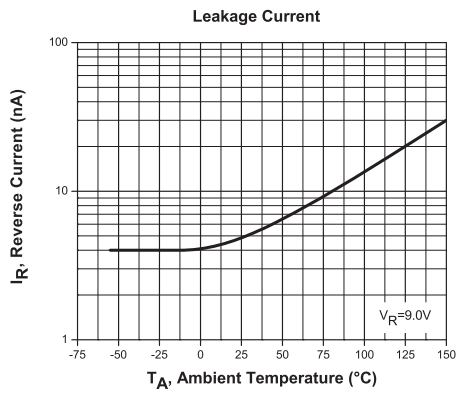
PRINCIPAL DEVICE TYPE

CMNTVS12V

R0 (3-January 2012)

PROCESS CPZ33R

Typical Electrical Characteristics



R0 (3-January 2012)